In the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims: 1 1. (Canceled). 1 2. (Canceled). (Canceled). 1 3. 1 4. (Canceled). 1 5. (Canceled). (Canceled). 1 6. 1 7. (Canceled). (Canceled). 1 8. 1 9. (Canceled). 10. (New) A reflective crystal display device comprising: 1 a semiconductor substrate; 2 at least one pair of pixel switching transistor and a capacitor 3 formed on the semiconductor substrate and electrically isolated from each other; 5 a first interlayer insulating layer formed on the pixel switching 6 transistor and the capacitor; 7 a wiring layer formed on the first interlayer insulating layer; 8 a second interlayer insulating layer formed over the wiring layer; 9

10		a light shielding layer formed on the second interlayer insulating
11		layer, the light shielding layer being divided into a plurality of layer
12		portions by gaps;
13		a third interlayer insulating layer formed over the light shielding
14		layer;
15		at least one pixel electrode formed on the third interlayer insulating
16		layer;
17		a common electrode formed over the pixel electrode;
18		a liquid crystal layer provided between the pixel electrode and the
19		common electrode;
20		a light-transmissive substrate formed on the common electrode;
21		and
22		at least one anti-reflection layer formed on the light shielding layer,
23		the anti-reflection layer being a double layer of a metallic film and a film
24		including Si that exhibits a refraction index different from a refraction
25		index of the third interlayer insulating layer, the film including Si covering
26		the gaps of the light shielding layer.
1	11.	(New) The reflective liquid crystal display device according to claim 10,
2		wherein the metallic film is a metallic nitride film.
1	12.	(New) The reflective liquid crystal display device according to claim 10,
2		wherein the metallic film is a titanium film.
1	13.	(New) The reflective liquid crystal display device according to claim 12,
2		wherein the titanium film is a titanium nitride film.
4	4.4	(Now) The reflective liquid emetal display device apparding to claim 40
1	14.	(New) The reflective liquid crystal display device according to claim 10,
2		wherein the film including Si is silicon oxynitride film.

1 2 3	15.	(New) The reflective liquid crystal display device according to claim 14, wherein the refraction index of the silicon oxynitride film is in the range from 1.7 to 1.9.
1	16.	(New) The reflective liquid crystal display device according to claim 14,
3		wherein a thickness of the silicon oxynitride film is in the range from 400 to 600 Å.
1	17.	(New) The reflective liquid crystal display device according to claim 10, wherein a thickness of the metallic film is small than 300 nm.
1	18.	(New) The reflective liquid crystal display device according to claim 10,
2		wherein a thickness of the metallic film is about 800 Å.
1	19.	(New) A reflective liquid crystal display device comprising:
2		a semiconductor substrate;
3		at least one pair of pixel switching transistor and a capacitor
4		formed on the semiconductor substrate and electrically isolated from
5		each other;
6		a first interlayer insulating layer formed on the pixel switching
7		transistor and the capacitor;
8		a wiring layer formed on the first interlayer insulating layer, the
9		wiring layer being divided into a plurality of layer portions by gaps;
10		a second interlayer insulating layer formed over the wiring layer;
1		a light shielding layer formed on the second interlayer insulating
12		layer;
13		a third interlayer insulating layer formed over the light shielding
4		layer;
15		at least one pixel electrode formed on the third interlayer insulating
16		layer;
17		a common electrode formed over the pixel electrode;

18		a liquid crystal layer provided between the pixel electrode and the
19		common electrode;
20		a light-transmissive substrate formed on the common electrode;
21		and
22		at least one anti-reflection layer formed on the wiring layer, the
23		anti-reflection layer being a double layer of a metallic film and a film
24		including Si that exhibits a refraction index different from a refraction
25		index of the third interlayer insulating layer, the film including Si covering
26		the gaps of the wiring layer.
1	20.	(New) The reflective liquid crystal display device according to claim 19,
2		wherein the metallic film is a metallic nitride film.
1	21.	(New) The reflective liquid crystal display device according to claim 19,
2		wherein the metallic film is a titanium film.
1	22.	(New) The reflective liquid crystal display device according to claim 21,
2		wherein the titanium film is a titanium nitride film.
1	23.	(New) The reflective liquid crystal display device according to claim 19,
2		wherein the film including Si is silicon oxynitride film.
1	24.	(New) The reflective liquid crystal display device according to claim 23,
2		wherein the refraction index of the silicon oxynitride film is in the range
3		from 1.7 to 1.9.
1	25.	(New) The reflective liquid crystal display device according to claim 23,
2		wherein a thickness of the silicon oxynitride film is in the range from 400
3		to 600 Å.
1	26.	(New) The reflective liquid crystal display device according to claim 19,
2		wherein a thickness of the metallic film is smaller than 300 nm.

1	27.	(New) The reflective liquid crystal display device according to claim 19,
2		wherein a thickness of the metallic film is about 800 Å.
1	28.	(New) A reflective crystal display device comprising:
2		a semiconductor substrate;
3		at least one pair of pixel switching transistor and a capacitor
4		formed on the semiconductor substrate and electrically isolated from
5		each other;
6		a first interlayer insulating layer formed on the pixel switching
7		transistor and the capacitor;
8		a wiring layer formed on the first interlayer insulating layer, the
9		wiring layer being divided into a plurality of layer portions by gaps;
10		a second interlayer insulating layer formed over the wiring layer;
11		a light shielding layer formed on the second interlayer insulating
12		layer, the light shielding layer being divided into a plurality of layer
13		portions by gaps;
14		a third interlayer insulating layer formed over the light shielding
15		layer;
16		at least one pixel electrode formed on the third interlayer insulating
17		layer;
18		a common electrode formed over the pixel electrode;
19		a liquid crystal layer provided between the pixel electrode and the
20		common electrode;
21		a light-transmissive substrate formed on the common electrode;
22		a first anti-reflection layer formed on the wiring layer, the first anti-
23		reflection layer being a double layer of a metallic film and a first film
24		including Si that exhibits a refraction index different from a refraction
25		index of the third interlayer insulating layer, the first film including Si
26		covering the gaps of the wiring layer; and
27		a second anti-reflection layer formed on the light shielding layer,
28		the second anti-reflection layer being a double layer of a metallic film and

a second film including Si that exhibits a refraction index different from a 29 refraction index of the third interlayer insulating layer, the second film 30 31 including Si covering the gaps of the light shielding layer. 1 29. (New) The reflective liquid crystal display device according to claim 28, 2 wherein each metallic film is a metallic nitride film. 1 30. (New) The reflective liquid crystal display device according to claim 28, 2 wherein each metallic film is a titanium film. 1 (New) The reflective liquid crystal display device according to claim 30, 31. 2 wherein the titanium film is a titanium nitride film. 1 32. (New) The reflective liquid crystal display device according to claim 28, 2 wherein each film including Si is silicon oxynitride film. 33. (New) The reflective liquid crystal display device according to claim 32, 1 2 wherein the refraction index of the silicon oxynitride film is in the range 3 from 1.7 to 1.9. 1 34. (New) The reflective liquid crystal display device according to claim 32, 2 wherein a thickness of the silicon oxynitride film is in the range from 400 3 to 600 Å. 1 (New) The reflective liquid crystal display device according to claim 28, 35. wherein a thickness of each metallic film is smaller than 300 nm. 2 (New) The reflective liquid crystal display device according to claim 28, 1 36. wherein a thickness of each metallic film is bout 800 Å. 2